

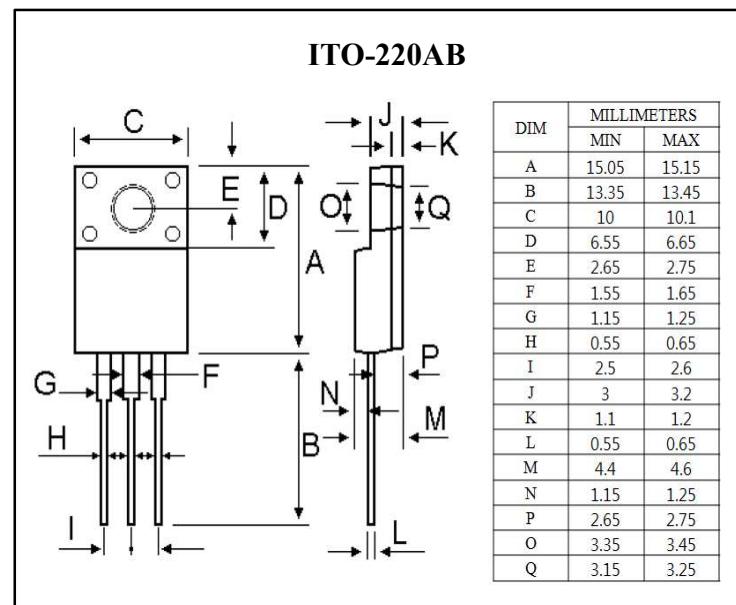


Dual Schottky Barrier Power Rectifier Reverse Voltage 50 Volts Forward Current 20 Ampere

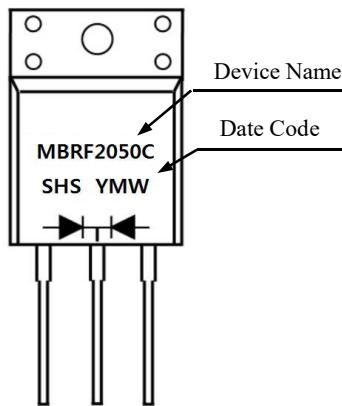
Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

Features

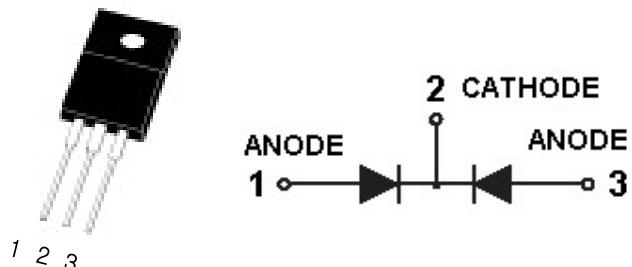
- Low Forward Voltage.
- Low Switching noise.
- High Current Capacity
- Guarantee Reverse Avalanche.
- Guard-Ring for Stress Protection.
- Low Power Loss & High efficiency.
- 150°C Operating Junction Temperature
- Low Stored Charge Majority Carrier Conduction.
- Plastic Material used Carries Underwriters Laboratory



Marking



Equivalent Circuit



Maximum Ratings & Electrical Characteristics

Parameter	Symbol	Rated Value	Unit	Remark
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	V	
Maximum RMS Voltage	V _{RMS}	35	V	
Maximum DC Blocking Voltage	V _{DC}	50	V	
Maximum Average Forward Rectified Current (Rated V _R)	I _{F(AV)}	10	A	Per Diode
		20	A	Total Device
Peak Repetitive Forward Current	I _{FM}	20	A	
Peak Forward Surge Current 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	200	A	
Maximum Instantaneous Forward Voltage at 10A	V _F	0.75	V	T _a =25°C
Maximum DC Reverse Current at Rated DC Blocking Voltage	I _R	0.15	mA	T _a =25°C
		20	mA	T _a =125°C
Operation Junction Temperature Range	T _J	-65 to +150	°C	
Storage Temperature Range	T _{STG}	-65 to +150	°C	



Ratings and Characteristics Curves (Ta=25°C unless otherwise noted)

Fig.1 Forward Current Derating Curve

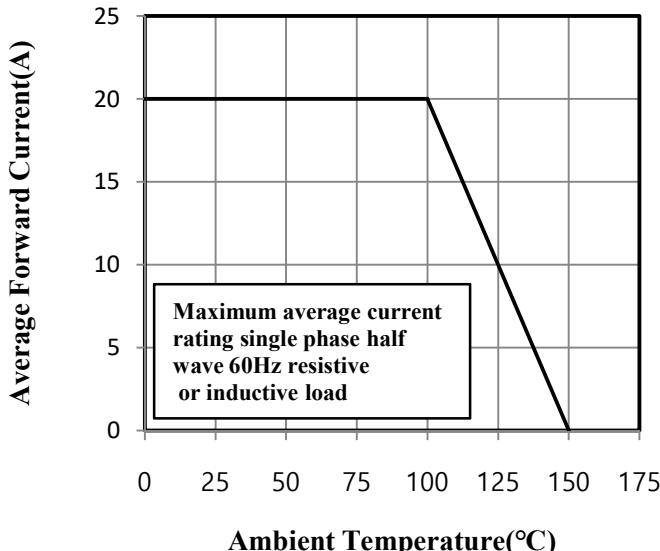


Fig.3 Typical Instantaneous Forward Characteristics

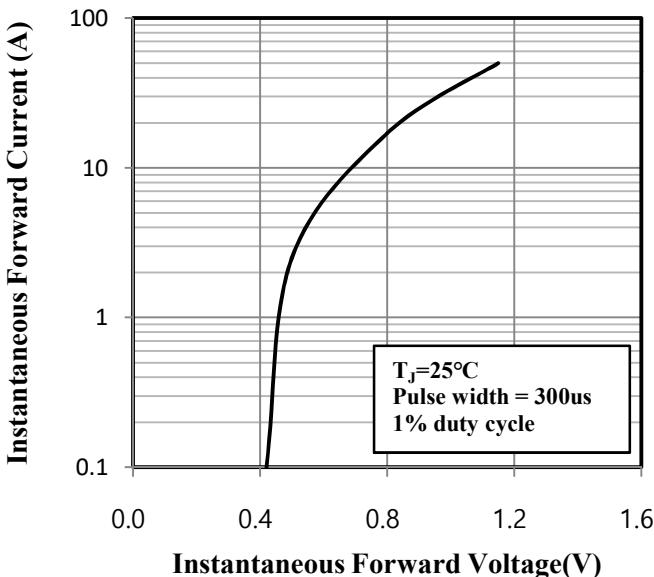


Fig.5 Typical Reverse Characteristics

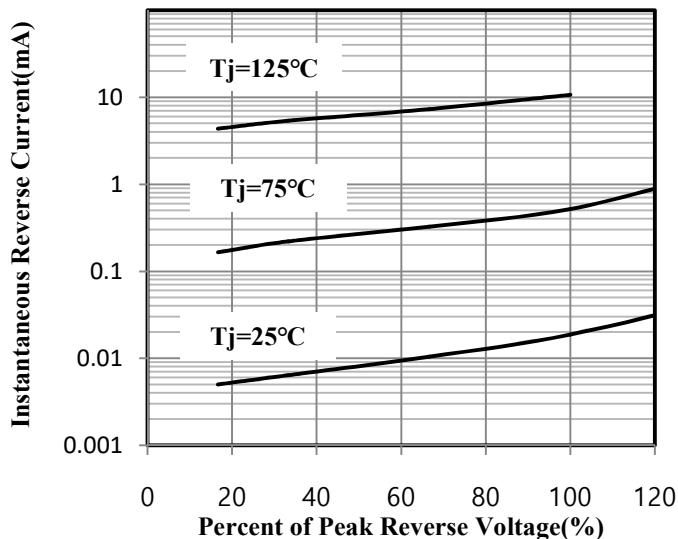


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

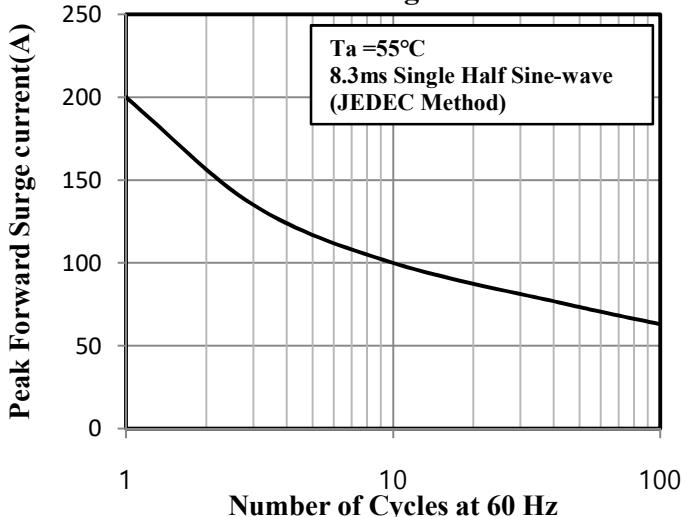


Fig.4 Typical Junction Capacitance

